

IN THE CLAIMS:

In accordance with 37 CFR 1.121 (c)(1)(i), please amend claims 3 and 4 as set forth below in clean form. Additionally, in accordance with 37 CFR 1.121(c)(1)(ii), amended claims 3 and 4 are set forth in a marked-up version in an Appendix attached herewith.

3. (Twice Amended) A semiconductor device, comprising:

a conductive layer pattern formed on a substrate;

an inter-layer insulating film which covers said conductive layer pattern and is formed on said substrate;

a first connection hole formed in an upper layer of said inter-layer insulating film above said conductive layer pattern;

a second connection hole which reaches said conductive layer pattern from the bottom portion of said first connection hole and then has a smaller diameter than that of said first connection hole and formed on said inter-layer insulation film;

a plug having conductivity formed in a state filling internal portions of said first connection hole and said second connection hole;

an upper insulating film formed on said inter-layer insulating film;

a third connection hole which reaches said plug and is formed on said inter-layer insulating film; and

a conductive portion which is connected to said plug and formed in said third connection hole.

4. (Twice Amended) A semiconductor device, comprising:

a conductive layer pattern formed on a substrate;

an inter-layer insulating film which covers said conductive layer pattern and is formed on

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said substrate;

a first connection hole formed in a upper layer of said inter-layer insulating film above said conductive layer pattern;

a second connection hole which reaches said conductive layer pattern from the bottom portion of said first connection hole and then has a smaller diameter than that of said first connection hole and formed on said inter-layer insulation film;

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a plug having conductivity formed in a state filling internal portions of said first connection hole and said second connection hole, wherein the upper surface of said plug is formed to almost the same height as the surface height of said inter-layer insulating film;

an upper insulating film formed on said inter-layer insulating film;

a third connection hole which reaches said plug and is formed on said inter-layer insulating film; and

a conductive contact portion which is connected to said plug and formed in said third connection hole.

REMARKS

This submission is in full response and timely to the non-final Office Action mailed on June 14, 2002. By this amendment, Applicants have amended the specification to comply with 37 CFR § 1.78(2)(i), and amended claims 3 and 4 to place the claims in better form. No new matter has been added. Claims 3-6 are pending.

Rejections Under 35 U.S.C. 102

Claims 3-6 were rejected under 35 U.S.C. § 102 as anticipated by *Prior Art Figs. 4-17*. Applicant traverses this rejection for the following reasons.

Independent claim 3 recites--a semiconductor device, comprising: a conductive layer